Electronic Supplementary Information

Manipulating the charge transfer at CuPc/graphene interface by O$_2$ plasma treatments

Hongying Mao*, Fang Hu$^{b,c}$, Quan-Lin Ye$^a$, Yifeng Xu$^a$, Xuxin Yang$^a$, Bin Lu*$_d$

$^a$Department of Physics, Hangzhou Normal University, Hangzhou 310036, China

$^b$Ningbo Institute of Technology, Zhejiang University, Ningbo 315100, China

$^c$Department of Physics, Zhejiang University, Hangzhou 310027, China

$^d$State Key Laboratory of Silicon Materials, Department of Materials Science and Engineering, Zhejiang University, Hangzhou 310027, China

*Corresponding author. Email address: phymaohy@gmail.com (H. Mao) Binlu@zju.edu.cn (B. Lu)
Figure S1 The sheet resistance of pristine graphene and O₂-G with increasing O₂ plasma exposure time.
Figure S2 UPS spectra at (a) the low kinetic energy region (secondary electron cutoff), and (b) the low binding energy region (valence band region) during the sequential deposition of 10.0 nm CuPc on graphene sample exposed to O$_2$ plasma (2 W) for 120 s.